INTEGRATED CIRCUITS

DATA SHEET

74ALVT16260

12-bit to 24-bit multiplexed D-type latches (3-State)

Product specification IC23 Data Handbook





2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

FEATURES

- ESD protection exceeds 2000V per Mil-Std-883C, Method 3015; exceeds 200V using machine model
- Latch-up protection exceeds 500mA per JEDEC Standard JESD-17.
- Distributed V_{CC} and GND pin configuration minimizes high-speed switching noise.
- Output capability (-32mA I_{OH}, 64mA I_{OL}).
- Bus hold inputs eliminate the need for external pull-up resistors.
- 5V I/O compatible
- Live insertion/extraction permitted
- Power-up 3-State
- Power-up Reset

DESCRIPTION

The 74ALVT16260 is a 12-bit to 24-bit multiplexed D-type latch used in applications where two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and/or demultiplexing of address and data information in microprocessor or bus-interface applications. This device is alto useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output enable (OE1B, OE2B, and OEA) inputs control the bus transceiver functions. The OE1B and OE2B control signals also allow bank control in the A to B direction

Address and/or data information can be stored using the internal storage latches. The latch enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch enable input is high, the latch is transparent. When the latch enable input goes low, the data present at the inputs is latched and remains latched until the latch enable input is returned high.

To ensure the high-impedance state during power-up or power-down, \overline{OE} should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

The 74ALVT16260 is available in a 56-pin Shrink Small Outline Package (SSOP) and 56-pin Thin Shrink Small Outline Package (TSSOP).

QUICK REFERENCE DATA

CVMDO	DADAMETER	CONDITIONS	TYP	UNIT	
SYMBOL	PARAMETER	T _{amb} = 25°C; GND = 0V	2.5V	3.3V	UNII
t _{PLH}	Propagation delay	C 50.75	3.5	2.8	
t _{PHL}	nAx to nBx nBx to nAx	$C_L = 50 \text{ pF}$	3.3	2.6	ns
C _{IN}	Input capacitance	$V_I = 0 \text{ V or } V_{CC}$	4	4	pF
C _{OUT}	Output capacitance	V _{I/O} = 0 V or 5.0 V	9	9	pF
I _{CCZ}	Total supply current	Outputs disabled	100	80	μА

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
56-Pin Plastic SSOP Type III	–40°C to +85°C	74ALVT16260 DL	AV16260 DL	SOT371-1
56-Pin Plastic TSSOP Type II	-40°C to +85°C	74ALVT16260 DGG	AV16260 DGG	SOT364-1

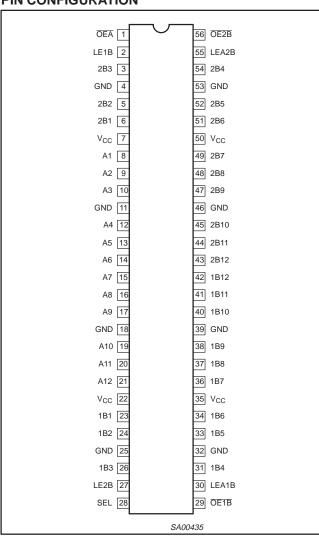
2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
8, 9, 10, 12, 13, 14, 15, 16, 17, 19, 20, 21	An	Data inputs/outputs (A)
23, 24, 26, 31, 33, 34, 36, 37, 38, 40, 41, 42	1Bn	Data inputs/outputs (B1)
6, 5, 3, 54, 52, 51, 49, 48, 47, 45, 44, 43	2Bn	Data inputs/outputs (B2)
1, 29, 56	OEA, OE1B, OE2B	Output enable input (active low)
2, 27, 30, 55	LE1B, LE2B, LEA1B, LEA2B	Latch enable inputs
28	SEL	B1/B2 input select input
4, 11, 18, 25, 32, 39, 46, 53	GND	Ground (0V)
7, 22, 35, 50	V _{CC}	Positive supply voltage

PIN CONFIGURATION



FUNCTION TABLES

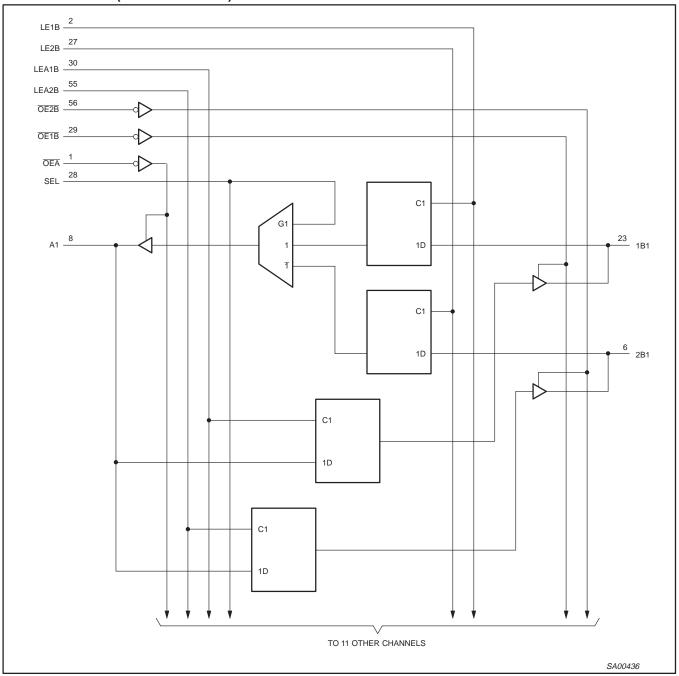
B to A ($\overline{OEB} = H$)

	INPUTS						
1B	2B	SEL	LE1B	LE2B	OEA	Α	
Н	Х	Н	Н	Х	L	Н	
L	Х	Н	Н	Х	L	L	
X	Х	Н	L	Х	L	A0	
X	Н	L	Х	Н	L	Н	
X	L	L	Х	Н	L	L	
X	Х	L	Х	L	L	A0	
Х	Х	Х	Х	Х	Н	Z	

A to B ($\overline{OEA} = H$)

		INPUTS			OUT	PUT
Α	LEA1B	LEA2B	OE1B	OE2B	1B	2B
Н	Н	Н	L	L	Н	Н
L	Н	Н	L	L	L	L
Н	н	L	L	L	Н	2B0
L	Н	L	L	L	L	2B0
Н	L	Н	L	L	1B0	Н
L	L	Н	L	L	1B0	L
X	L	L	L	L	1B0	2B0
X	Х	Х	Н	Н	Z	Z
X	Х	Х	L	Н	Active	Z
X	Х	Х	Н	L	Z	Active
X	Х	Х	L	L	Active	Active

LOGIC DIAGRAM (POSITIVE LOGIC)



2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +4.6	V
I _{IK}	DC input diode current	V _I < 0	-50	mA
VI	DC input voltage ³		-0.5 to +7.0	V
lok	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	Output in Off or High state	-0.5 to +7.0	V
	DC output ourrent	Output in Low state	128	A
Гоит	DC output current	Output in High state	-64	mA
T _{stg}	Storage temperature range		-65 to +150	°C

NOTES:

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	2.5V RAN	GE LIMITS	3.3V RANGE LIMITS		UNIT
J ST WIBOL	TANAMETER	MIN	MAX	MIN	MAX	ONIT
V _{CC}	DC supply voltage	2.3	2.7	3.0	3.6	V
VI	Input voltage	0	5.5	0	5.5	V
V _{IH}	High-level input voltage	1.7		2.0		V
V _{IL}	Input voltage		0.7		0.8	V
I _{OH}	High-level output current		-8		-32	mA
lai	Low-level output current		8		32	mA
l _{OL}	Low-level output current; current duty cycle ≤ 50%; f ≥ 1kHz		24		64	ША
Δt/Δν	Input transition rise or fall rate; Outputs enabled		10		10	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	-40	+85	°C

Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the
device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
absolute-maximum-rated conditions for extended periods may affect device reliability.

^{2.} The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

^{3.} The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

DC ELECTRICAL CHARACTERISTICS (3.3V \pm 0.3V RANGE)

					LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS		Temp =	-40°C to	+85°C	UNIT
				MIN	TYP ¹	MAX	
V _{IK}	Input clamp voltage	$V_{CC} = 3.0V; I_{IK} = -18mA$			-0.85	-1.2	V
V _{OH}	High-level output voltage	$V_{CC} = 3.0 \text{ to } 3.6\text{V}; I_{OH} = -100\mu\text{A}$		V _{CC} _0.2	V _{CC}		V
VOH	I light-level output voltage	$V_{CC} = 3.0V; I_{OH} = -32mA$		2.0	2.3		V
		$V_{CC} = 3.0V; I_{OL} = 100\mu A$			0.07	0.2	
V _{OL}	Low-level output voltage	$V_{CC} = 3.0V; I_{OL} = 16mA$			0.25	0.4	V
VOL	Low-level output voltage	$V_{CC} = 3.0V; I_{OL} = 32mA$			0.3	0.5	V
		$V_{CC} = 3.0V; I_{OL} = 64mA$			0.4	0.55	
V _{RST}	Power-up output low voltage ⁶	$V_{CC} = 3.6V$; $I_O = 1mA$; $V_I = V_{CC}$ or GND				0.55	V
		$V_{CC} = 3.6V$; $V_I = V_{CC}$ or GND	Control pins		0.1	±1	
ı.	Input lookogo ourrent	V _{CC} = 0 or 3.6V; V _I = 5.5V			0.1	10	μА
11	Input leakage current	$V_{CC} = 3.6V; V_I = V_{CC}$	Data pins ⁴		0.1	1	
		V _{CC} = 3.6V; V _I = 0V	Data piris		0.1	-5	
I _{OFF}	Off current	$V_{CC} = 0V; V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5V$			0.1	±100	μΑ
	Bus Hold current	V _{CC} = 3V; V _I = 0.8V		75	130		
I _{HOLD}	Data inputs ⁷	V _{CC} = 3V; V _I = 2.0V		-75	-140		μΑ
	Data iriputs	$V_{CC} = 0V \text{ to } 3.6V; V_{CC} = 3.6V$		±500			
I _{EX}	Current into an output in the High state when V _O > V _{CC}	V _O = 5.5V; V _{CC} = 3.0V			10	125	μА
I _{PU/PD}	Power up/down 3-State output current ³	$V_{CC} \le 1.2V$; $V_O = 0.5V$ to V_{CC} ; $V_I = GND$ OE/OE = Don't care	or V _{CC}		1	±100	μА
l _{OZH}	3-State output High current	$V_{CC} = 3.6V; V_{O} = 3.0V; V_{I} = V_{IL} \text{ or } V_{IH}$			0.5	5	μΑ
I _{OZL}	3-State output Low current	$V_{CC} = 3.6V; V_{O} = 0.5V; V_{I} = V_{IL} \text{ or } V_{IH}$			0.5	-5	μΑ
I _{CCH}		$V_{CC} = 3.6V$; Outputs High, $V_I = GND$ or $V_{CC} = 0.00$	/ _{CC,} I _{O =} 0		0.04	0.1	
I _{CCL}	Quiescent supply current	$V_{CC} = 3.6V$; Outputs Low, $V_I = GND$ or V	CC, I _{O =} 0		3.7	6	mA
I _{CCZ}	1	V _{CC} = 3.6V; Outputs Disabled; V _I = GND	or V_{CC} , $I_{O} = 0^5$		0.04	0.1	┨
Δl _{CC}	Additional supply current per input pin ²	V_{CC} = 3V to 3.6V; One input at V_{CC} -0.6\ Other inputs at V_{CC} or GND	/,		0.04	0.4	mA

NOTES:

- All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.
 This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND
 This parameter is valid for any V_{CC} between 0V and 1.2V with a transition time of up to 10msec. From V_{CC} = 1.2V to V_{CC} = 3.3V ± 0.2V a transition time of 100µsec is permitted. This parameter is valid for T_{amb} = 25°C only.

- 4. Unused pins at V_{CC} or GND.
 5. I_{CCZ} is measured with outputs pulled up to V_{CC} or pulled down to ground.
 6. For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.
- 7. This is the bus hold overdrive current required to force the input to the opposite logic state.

2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

AC ELECTRICAL CHARACTERISTICS (3.3V \pm 0.3V RANGE)

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF; R_L = 500 Ω

SYMBOL	PARA	METER	T _{ar}	$T_{amb} = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ $V_{CC} = +3.3\text{V} \pm 0.3\text{V}$		
l	FROM (INPUT)	TO (OUTPUT)	MIN	TYP	MAX]
t _{PLH}	A or B	B or A	1	2.8	4.8	ns
t _{PHL}	A Or B	B OF A	1	2.6	4.6	ns
t _{PLH}	ΙĒ	A or B	1.1	2.9	4.6	ns
t _{PHL}	LE	AOIB	1.1	3.1	4.7	ns
	SEL (B1)	A	1.3	2.3	3.4	ns
t _{PLH}	SEL (B2)	A	1.1	2.4	3.8	ns
	SEL (B1)	A	1.5	2.4	3.6	ns
t _{PHL}	SEL (B2)	А	1.6	2.4	3.6	ns
t _{PZH}	OF.	A an D	1	2.3	4.2	ns
t _{PZL}	ŌĒ	A or B	1.6	2.3	4.0	ns
t _{PHZ}	ŌĒ	A on D	2.2	4.4	6.0	ns
t _{PLZ}	OE	A or B	1.3	3.1	5.0	ns

AC SETUP CHARACTERISTICS (3.3V $\pm\,0.3V$ RANGE)

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF; R_L = 500 Ω

SYMBOL	PARAMETER	$T_{amb} = -40^{\circ}$ $V_{CC} = +3$.	°C to +85°C 3V ± 0.3V	UNIT
		MIN	MAX	
t _w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	3.3		ns
t _{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B↓	1		ns
t _h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B↓ 1		ns	

2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

DC ELECTRICAL CHARACTERISTICS (2.5V \pm 0.2V RANGE)

					LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS	TEST CONDITIONS		-40°C to	+85°C	UNIT
					TYP ¹	MAX	
V _{IK}	Input clamp voltage	$V_{CC} = 2.3V; I_{IK} = -18mA$			-0.85	-1.2	V
V _{OH}	High-level output voltage	$V_{CC} = 2.3 \text{ to } 3.6 \text{V}; I_{OH} = -100 \mu\text{A}$		V _{CC} -0.2	V _{CC}		V
VOH	I light-level output voltage	$V_{CC} = 2.3V; I_{OH} = -8mA$		1.8	2.1		ľ
V _{OL}	Low-level output voltage	$V_{CC} = 2.3V; I_{OL} = 100\mu A$			0.07	0.2	
VOL	Low-level output voltage	$V_{CC} = 2.3V; I_{OL} = 24mA$			0.3	0.5	
V _{RST}	Power-up output low voltage ⁷	$V_{CC} = 2.7V$; $I_{O} = 1$ mA; $V_{I} = V_{CC}$ or GNE)			0.55	V
		$V_{CC} = 2.7V$; $V_I = V_{CC}$ or GND	Control pins		0.1	±1	
1	Input lookage ourrent	V _{CC} = 0 or 2.7V; V _I = 5.5V			0.1	10	
l _l	Input leakage current	$V_{CC} = 2.7V; V_I = V_{CC}$	Data nina4		0.1	1	μΑ
		$V_{CC} = 2.7V; V_I = 0$	Data pins ⁴		0.1	-5	1
I _{OFF}	Off current	$V_{CC} = 0V$; V_{I} or $V_{O} = 0$ to 4.5V	•		0.1	±100	μΑ
I _{HOLD}	Bus Hold current	$V_{CC} = 2.3V; V_I = 0.7V$			90		μА
	Data inputs ⁶	$V_{CC} = 2.3V; V_I = 1.7V$			-10		μΑ
I _{EX}	Current into an output in the High state when V _O > V _{CC}	V _O = 5.5V; V _{CC} = 2.3V			10	125	μΑ
I _{PU/PD}	Power up/down 3-State output current ³	$V_{CC} \le 1.2V$; $V_O = 0.5V$ to V_{CC} ; $V_I = GNI$ $OE/\overline{OE} = Don't$ care	O or V _{CC} ;		1	100	μΑ
I _{OZH}	3-State output High current	$V_{CC} = 2.7V; V_{O} = 2.3V; V_{I} = V_{IL} \text{ or } V_{IH}$			0.5	5	μΑ
I _{OZL}	3-State output Low current	$V_{CC} = 2.7V; V_{O} = 0.5V; V_{I} = V_{IL} \text{ or } V_{IH}$			0.5	- 5	μΑ
I _{CCH}		$V_{CC} = 2.7V$; Outputs High, $V_I = GND$ or V_{CC} , $I_{O} = 0$			0.04	0.1	
I _{CCL}	Quiescent supply current	$V_{CC} = 2.7V$; Outputs Low, $V_I = GND$ or V_{CC} , $I_{O} = 0$			2.7	4.5	mA
I _{CCZ}	1	$V_{CC} = 2.7V$; Outputs Disabled; $V_I = \text{GND or } V_{CC}$, $I_{O} = 0^5$			0.04	0.1	1
ΔI_{CC}	Additional supply current per input pin ²	V_{CC} = 2.3V to 2.7V; One input at V_{CC} Other inputs at V_{CC} or GND	0.6V,		0.04	0.4	mA

- All typical values are at V_{CC} = 2.5V and T_{amb} = 25°C.
 This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND
 This parameter is valid for any V_{CC} between 0V and 1.2V with a transition time of up to 10msec. From V_{CC} = 1.2V to V_{CC} = 2.5V ± 0.3V a transition time of 100µsec is permitted. This parameter is valid for T_{amb} = 25°C only.
 Unused pins at V_{CC} or GND.
- 5. I_{CCZ} is measured with outputs pulled up to V_{CC} or pulled down to ground.
 6. Not guaranteed.
- 7. For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

AC ELECTRICAL CHARACTERISTICS (2.5V \pm 0.2V RANGE)

 $\label{eq:gnd} \text{GND} = \text{0V}; \, t_{\text{R}} = t_{\text{F}} = \text{2.5ns}; \, \text{C}_{\text{L}} = \text{50pF}; \, \text{R}_{\text{L}} = \text{500}\Omega$

SYMBOL	PARAI	PARAMETER		T_{amb} = -40°C to +85°C V_{CC} = +2.5V \pm 0.2V			
	FROM (INPUT) TO (OUTPUT)		MIN	TYP	MAX		
t _{PLH}	A or B	B or A	1	3.5	5.3	ns	
t _{PHL}	AUID	BUIA	1	3.3	5.4	ns	
t _{PLH}	ΙĒ	A or B	1.1	3.9	6.0	ns	
t _{PHL}	LE	AUIB	1.1	4.2	6.2	ns	
	SEL (B1)	А	1.3	2.9	4.5	ns	
t _{PLH}	SEL (B2)	А	1.1	3.3	4.8	ns	
	SEL (B1)	А	1.5	3.0	4.5	ns	
t _{PHL}	SEL (B2)	А	1.6	3.2	4.6	ns	
t _{PZH}	ŌĒ	A or D	1	3.1	5.0	ns	
t _{PZL}	UE UE	A or B	1.6	2.0	3.0	ns	
t _{PHZ}	ŌĒ	A or D	2.2	4.0	6.6	ns	
t _{PLZ}	OE .	A or B	1.3	2.0	3.4	ns	

AC SETUP CHARACTERISTICS (2.5V \pm 0.2V RANGE)

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF; R_L = 500 Ω

SYMBOL	PARAMETER	T _{amb} = -40° V _{CC} = +2.	°C to +85°C 5V ± 0.2V	UNIT
		MIN	MAX	
t _w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	3.3		ns
t _{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B↓	1		ns
t _h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B↓	1		ns

2.5V/3.3V 12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

AC WAVEFORMS

 $V_M = 1.5V$ for all waveforms

The outputs are measured one at a time with one transition per measurement.

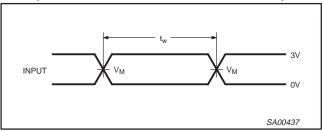


Figure 1. Pulse duration

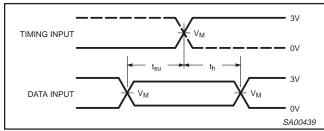
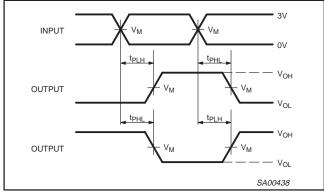
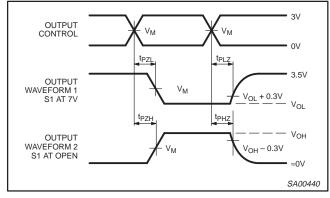


Figure 3. Setup and hold times



All input pulses are supplied by generators having the following characteristics: PRR \leq 10MHz, Z_O = 50Ω, t_f \leq 2.5ns, t_f \leq 2.5ns.

Figure 2. Propagation delay times; inverting and non-inverting outputs



Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

Figure 4. Enable and disable times; low- and high-level enabling

TEST LOAD CIRCUIT

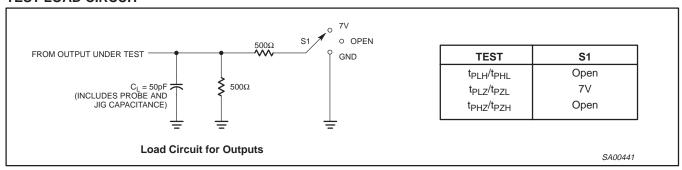


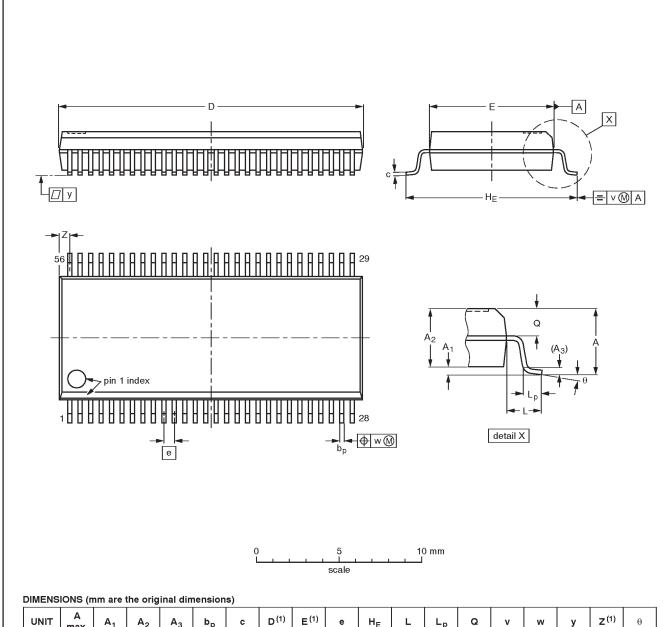
Figure 5. Test load circuit

12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

SSOP56: plastic shrink small outline package; 56 leads; body width 7.5 mm

SOT371-1



UNIT	A max.	Α ₁	A ₂	A ₃	рb	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2.8	0.4 0.2	2.35 2.20	0.25	0.3 0.2	0.22 0.13	18.55 18.30	7.6 7.4	0.635	10.4 10.1	1.4	1.0 0.6	1.2 1.0	0.25	0.18	0.1	0.85 0.40	8° 0°

Note

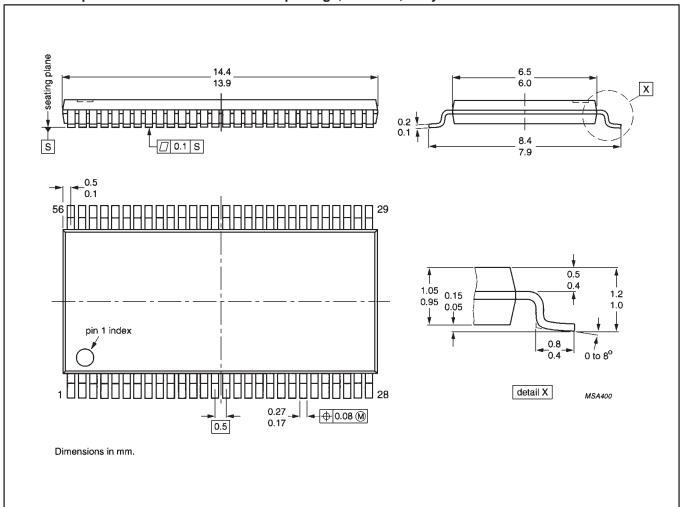
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT371-1		MO-118AB				93-11-02 95-02-04

12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

plastic thin shrink small outline package; 56 leads; body width 6.1mm SOT364-1



12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

NOTES

12-bit to 24-bit multiplexed D-type latches (3-State)

74ALVT16260

Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
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